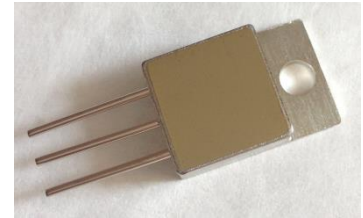
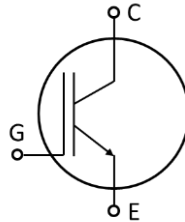


Discrete IGBT

Features:

- 1200V Trench & Field stop technology
- Low switching losses
- Positive temperature coefficient



TO-254

Applications:

- Induction cooker
- Electric welding machine

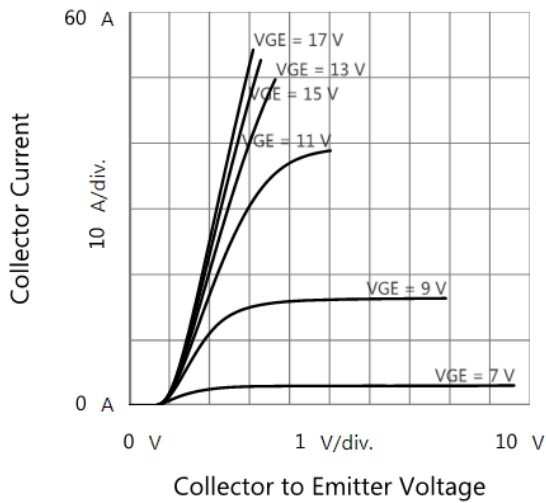
Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter voltage	V_{CE}	1200	V
Continuous DC collector current	$I_{C\ nom}$	25	A
Gate emitter voltage	V_{GE}	± 20	V

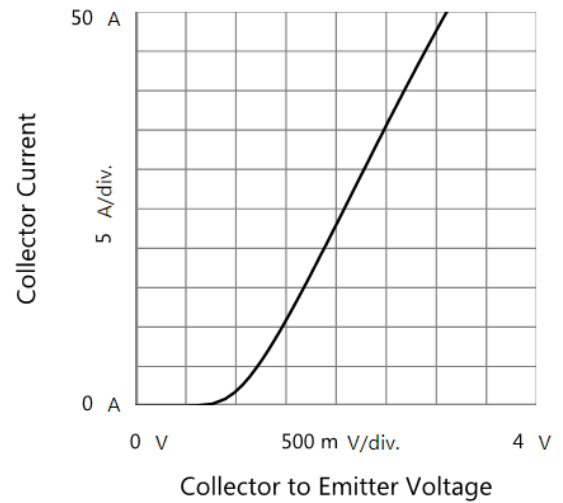
Characteristic Values, $T_{vj}=25^{\circ}C$

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
Collector-Emitter saturation voltage	$V_{GE}=15V, I_C=20A$	V_{CEsat}		1.87		V
Collector-Emitter saturation voltage	$V_{GE}=15V, I_C=25A$	V_{CEsat}		2.06		
Gate-Emitter threshold voltage	$I_C=0.8mA, V_{GE}= V_{CE}$	$V_{GE(th)}$	5.0	5.4	6.0	
Gate-emitter cut-off current	$V_{CE}=1200V, V_{GE}= 0V$	I_{CES}			2.0	uA
Gate-Emitter leakage current	$V_{CE}=0V, V_{GE}= 20V$	I_{GES}			100	nA
Integrated gate resistor		r_G		0.7		Ω
Input capacitance	$V_{CE}=25V, V_{GE}=0V, f=1MHz$	C_{ies}		2727		pF
Output capacitance		C_{oes}		91		
Reverse transfer capacitance		C_{res}		44		

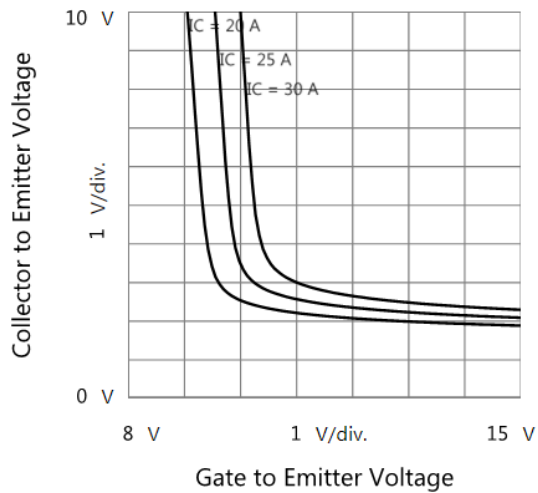
Output Characteristics



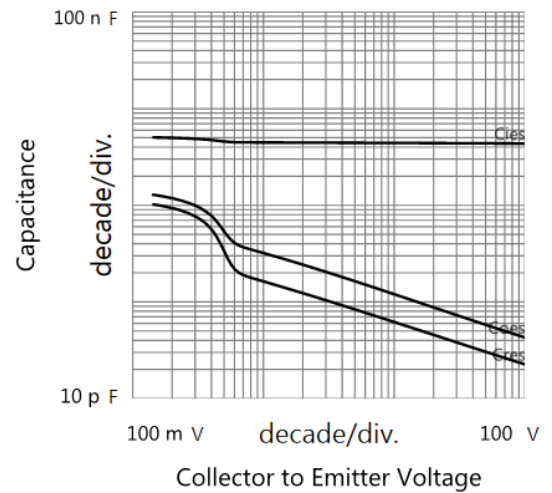
Output Characteristics V_{ge}=15V



Collector to Emitter Voltage vs. Gate to Emitter Voltage



Capacitances



Package outlines

TO-254

